SPECIFICATION

Device Name : SILICON DIODE

Type Name : YG902C2RF109

Spec. No. : MS5D0928

Fuji Electric Co.,Ltd.
Matsumoto Factory

	DATE	NAME	APPROVED
DRAWN	May-13-99	S.Matsuoka	S.Tsuji
CHECKED	May-13-99	K.Sakuma	

Fuji Electric Co.,Ltd.

DWG.NO. MS5D0928 1/8

H04-004-07

Revised Records

Date	Classi—fication	Ind.	Content	Applied date	Drawn	Checked	Approved
MAY. —13 —1999	enactment	——	————	Issued date	——	K. Sakamaw	S. Tko

1. SCOPE

This specification provides the ratings and the test requirement for FUJI SILICON DIODE YG902C2RF109

2. OUT VIEW · MARKING · MOLDING RESIN · FORMING · CHARACTERISTICS

(1) Out view is shown MS5D0928 4/8
(2) Marking is shown MS5D0928 4/8
It is marked to type name or abbreviated type name, polarity and Lot No.
(3) Formig is shown MS5D0928 5/8
(4) Characteristics is shown MS5D0928 6/8 ~ 8/8
(4) Molding resin Epoxy resin UL94 : 94V-0

3. RATINGS

3.1 MAXIMUM RATINGS

I T E M	SYMBOL	CONDITIONS	RATINGS	UNIT
Repetitive peak reverse voltage	V_{RRM}		200	V
Non-repetitive peak reverse voltage	V_{RSM}		200	V
Isolating voltage	Viso	Terminals-to-Case, AC.1min	1500	V
Average forward current	Io	Square wave duty=1/2 Tc=115℃	10 *	A
Non-repetitive surge current	I_{FSM}	Sine wave, 10ms	50	A
Operating junction temperature	Tj		-40to+150	℃
Storage temperature	Tstg		-40to+150	℃

* Output current of centertap full wave connection.

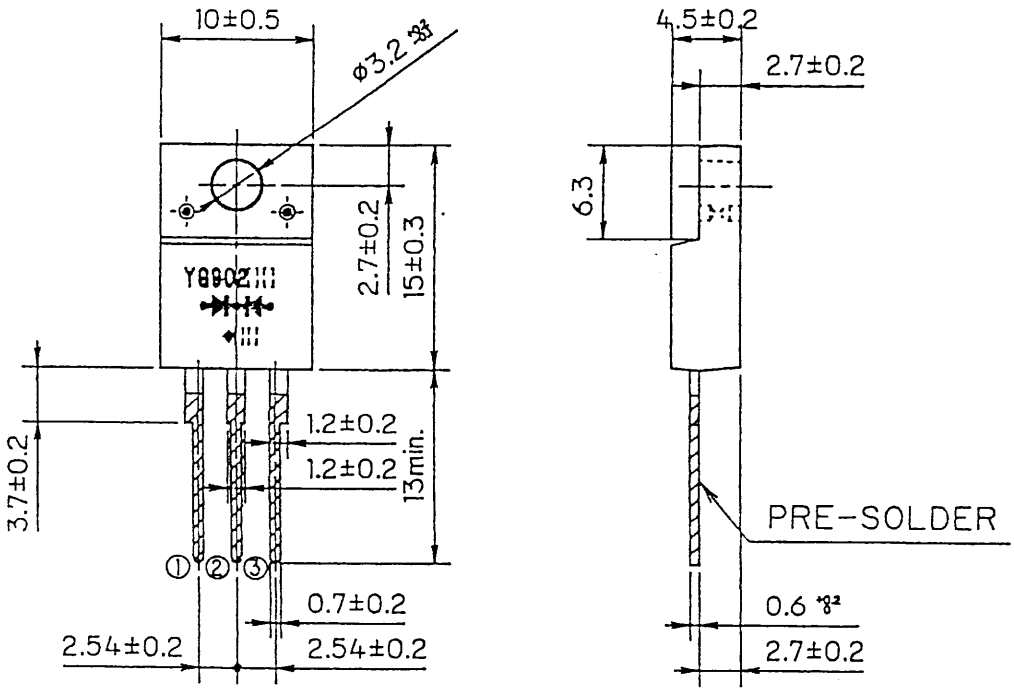
3.2 ELECTRICAL CHARACTERISTICS (at Ta= 25℃ unless otherwise specified.)

I T E M	SYMBOL	C O N D I T I O N S	MAXIMUM	UNIT
Forward voltage	V_F	I_F = 5 A	0.95	V
Reverse current	I_R	V_R = V_{RRM}	100	μA
Reverse recovery time	trr	I_F =0.1A, I_R =0.2A, Irec=0.05A	35	ns
Thermal resistance	Rth(j-c)	Junction to case	3.5	℃/W

3.3 MECHANICAL CHARACTERISTICS

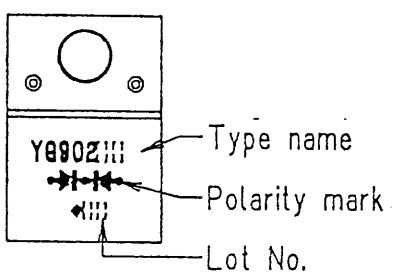
Mounting torque	Recommended torque	0.3 ~ 0.5	N · m
Approximate weight		2.0	g

OUT VIEW



DIMENTIONS ARE IN MILLIMETERS.

MARKING

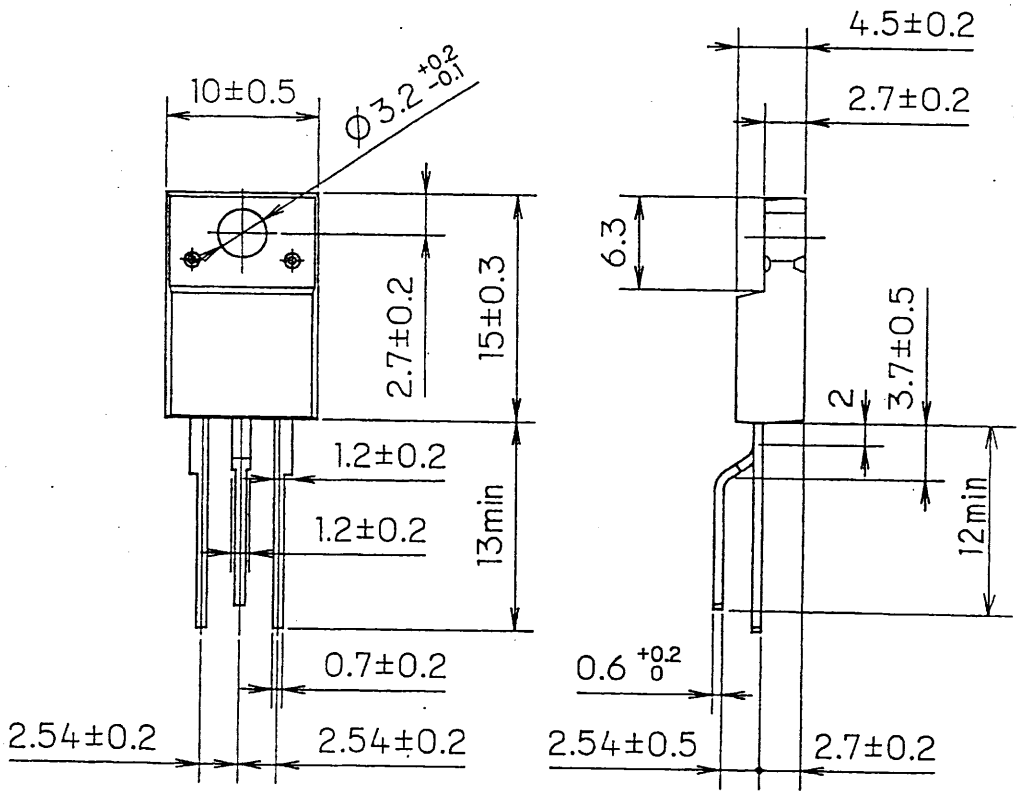


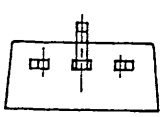
CONNECTION

YG902C

TO-220F15

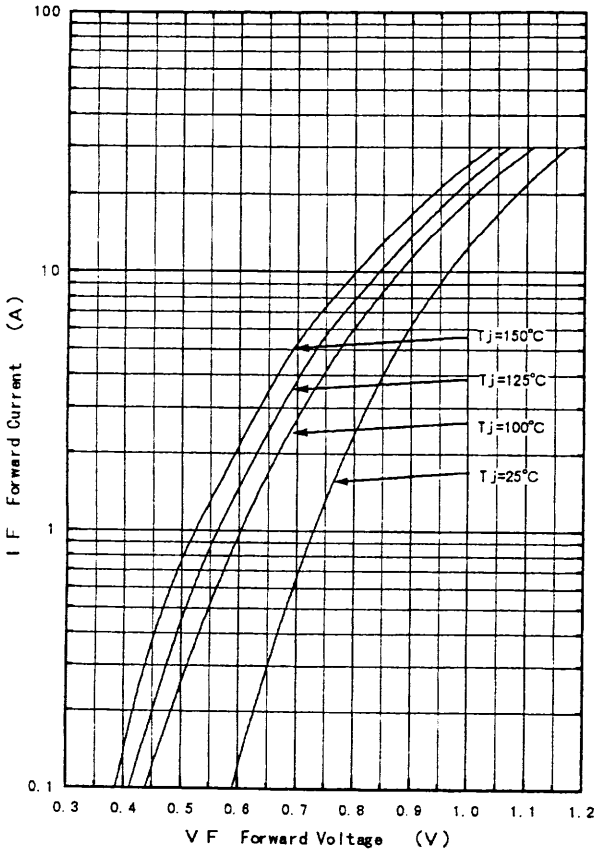
F109フォーミング寸法図



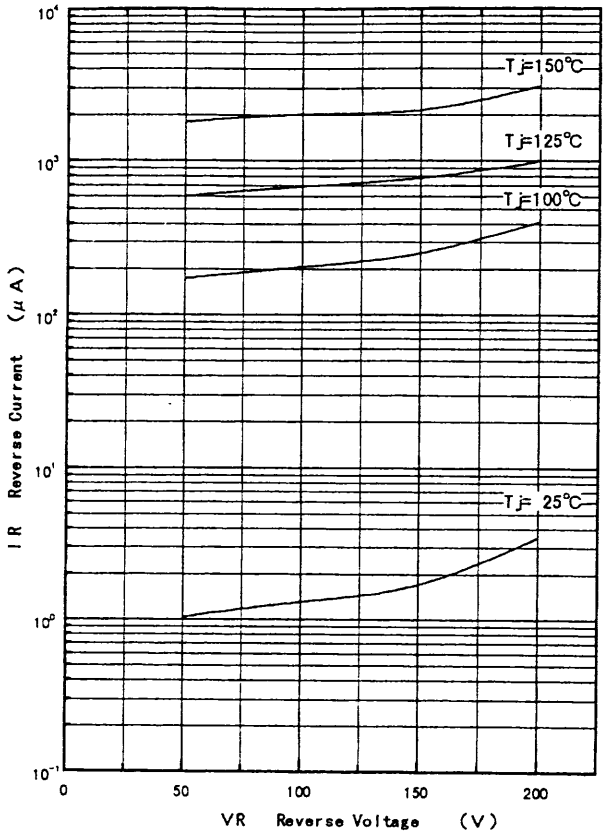


寸法単位(mm)
Dimension(mm)

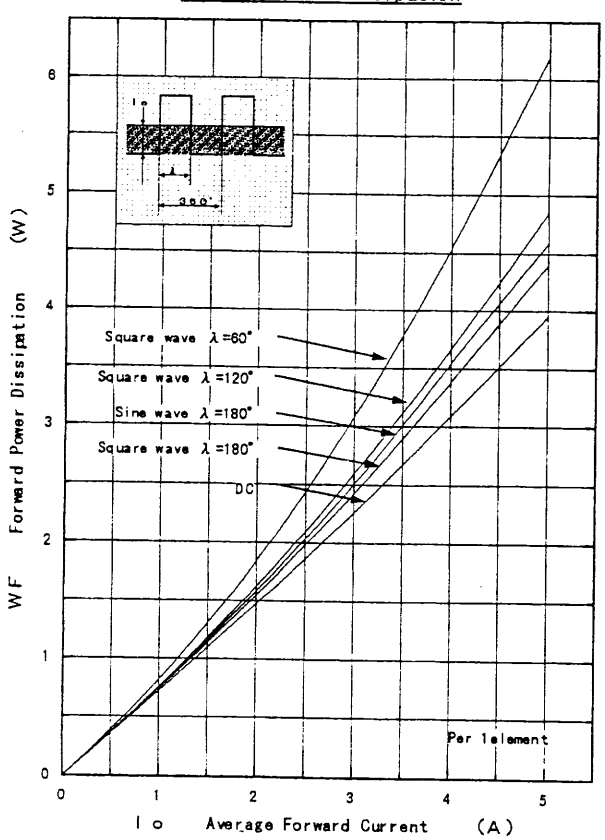
Forward Characteristic (typ.)



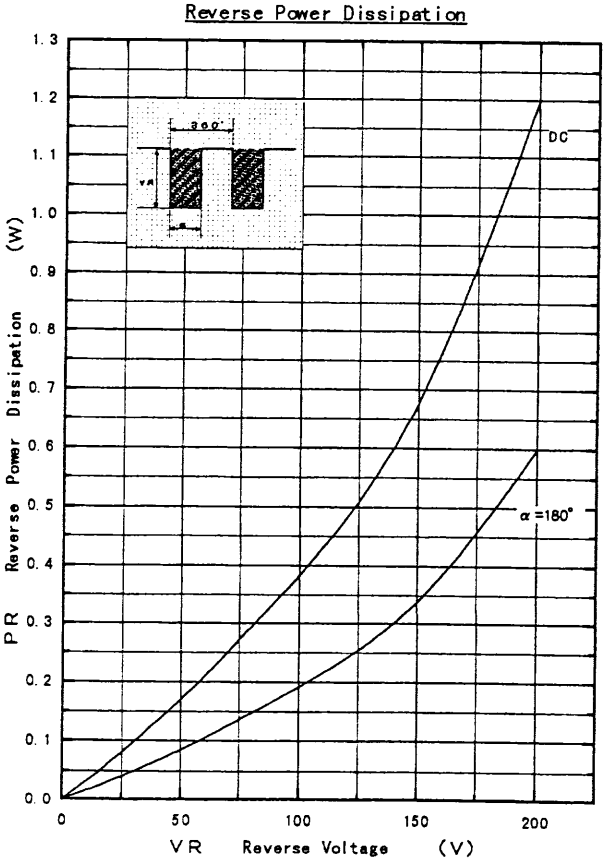
Reverse Characteristic (typ.)



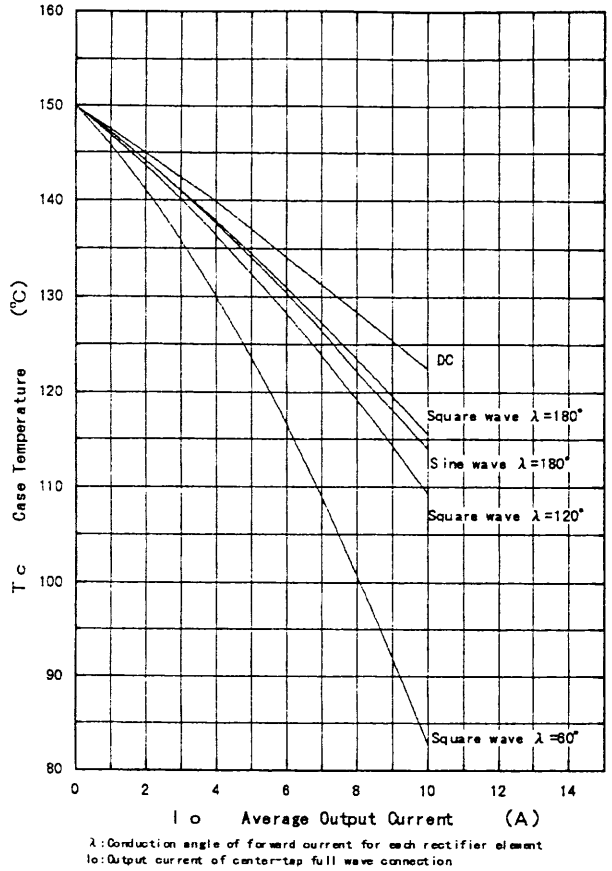
Forward Power Dissipation



Reverse Power Dissipation

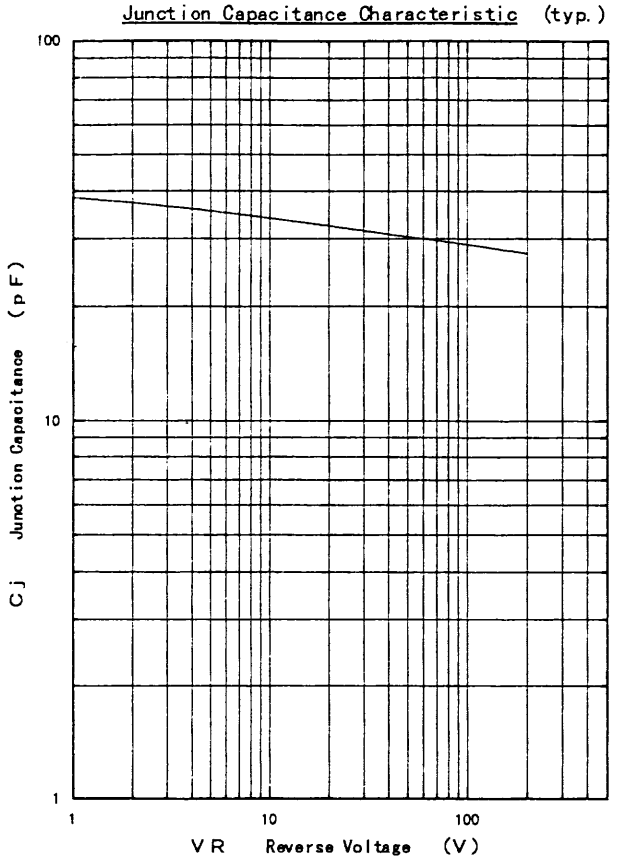


Current Derating (Io-Tc)

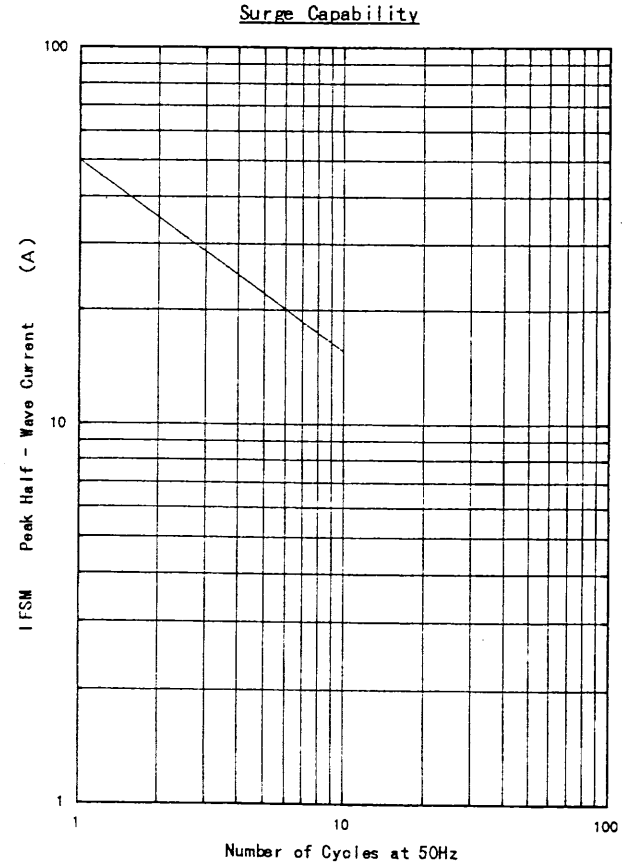


λ : Conduction angle of forward current for each rectifier element
Io : Output current of center-tap full wave connection

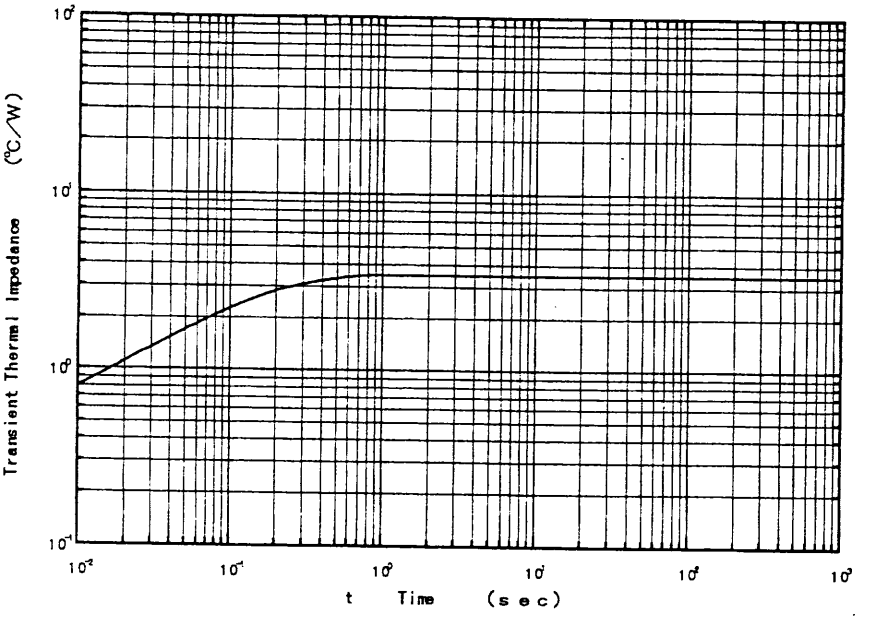
Junction Capacitance Characteristic (typ.)



Surge Capability



Transient Thermal Impedance



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